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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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# **Low Noise Transistors**

## **NPN Silicon**

#### **Features**

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT5088L MMBT5089L	V <sub>CEO</sub>	30 25	Vdc
Collector-Base Voltage MMBT5088L MMBT5089L	V <sub>CBO</sub>	35 30	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	4.5	Vdc
Collector Current – Continuous	I <sub>C</sub>	50	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

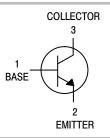


#### ON Semiconductor®

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SOT-23 (TO-236) CASE 318 STYLE 6



### **MARKING DIAGRAM**



1x = Device Code

x = Q for MMBT5088L SMMBT5088L

x = R for MMBT5089L SMMBT5089L

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

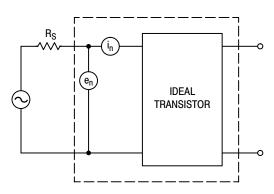
Device	Package	Shipping <sup>†</sup>
MMBT5088LT1G,	SOT-23	3,000 / Tape &
SMMBT5088LT1G	(Pb-Free)	Reel
NSVMMBT5088LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5089LT1G,	SOT-23	3,000 / Tape &
SMMBT5089LT1G	(Pb-Free)	Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		•	•
Collector – Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT5088L MMBT5089L	V <sub>(BR)CEO</sub>	30 25	_ _	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	MMBT5088L MMBT5089L	V <sub>(BR)CBO</sub>	35 30	- -	Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 15 \text{ Vdc}, I_E = 0)$	MMBT5088L MMBT5089L	I <sub>CBO</sub>	- -	50 50	nAdc
Emitter Cutoff Current $(V_{EB(off)} = 3.0 \text{ Vdc}, I_C = 0)$ $(V_{EB(off)} = 4.5 \text{ Vdc}, I_C = 0)$	MMBT5088L MMBT5089L	I <sub>EBO</sub>	- -	50 100	nAdc
ON CHARACTERISTICS		•		•	•
DC Current Gain (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc)	MMBT5088L MMBT5089L	h <sub>FE</sub>	300 400	900 1200	-
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5088L MMBT5089L		350 450	- -	
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5088L MMBT5089L		300 400	-	
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)		V <sub>CE(sat)</sub>	-	0.5	Vdc
Base – Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$		V <sub>BE(sat)</sub>	-	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain — Bandwidth Product ( $I_C = 500 \mu Adc$ , $V_{CE} = 5.0 Vdc$ , $f = 20 MHz$ )		f <sub>T</sub>	50		MHz
Collector–Base Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz emitter guarded)		C <sub>cb</sub>	-	4.0	pF
Emitter-Base Capacitance ( $V_{EB} = 0.5 \text{ Vdc}, I_{C} = 0, f = 1.0 \text{ MHz}$ collector guarded)		C <sub>eb</sub>	-	10	pF
Small Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 1.0 kHz)	MMBT5088L MMBT5089L	h <sub>fe</sub>	350 450	1400 1800	-
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 10 k $\Omega$ , f = 1.0 kHz)	MMBT5088L MMBT5089L	NF	_ _	3.0 2.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

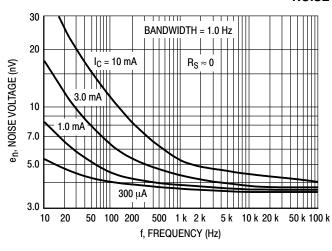


**Figure 1. Transistor Noise Model** 

#### **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

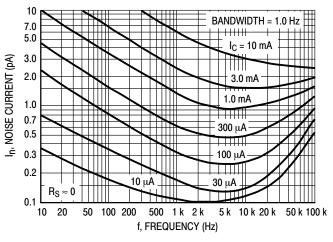
#### **NOISE VOLTAGE**



BANDWIDTH = 1.0 Hz 20  $R_S\approx 0\,$ en, NOISE VOLTAGE (nV) f = 10 Hz 10 100 Hz 7.0 5.0 3.0 0.02 0.01 0.05 0.1 0.2 0.5 1.0 2.0 5.0 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

Figure 3. Effects of Collector Current



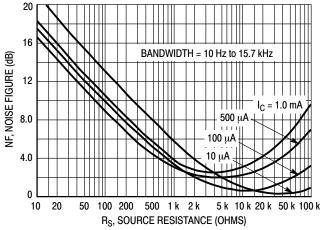
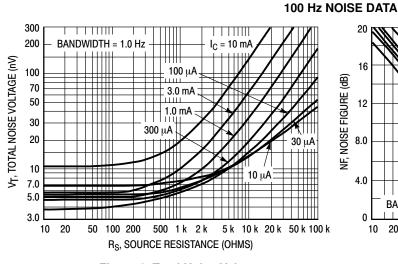


Figure 4. Noise Current

Figure 5. Wideband Noise Figure



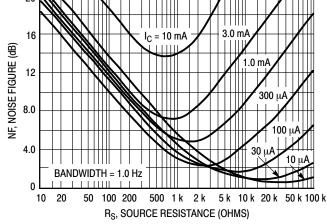


Figure 6. Total Noise Voltage

Figure 7. Noise Figure

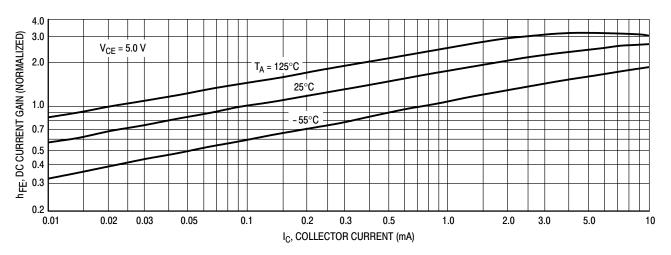


Figure 8. DC Current Gain

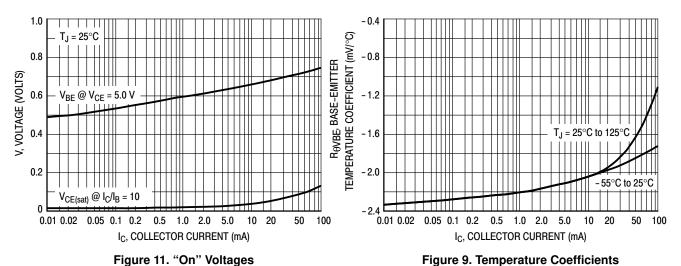


Figure 11. "On" Voltages

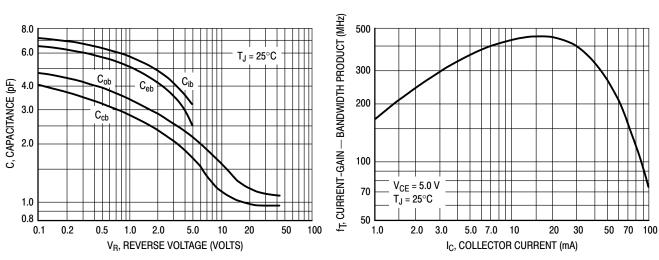
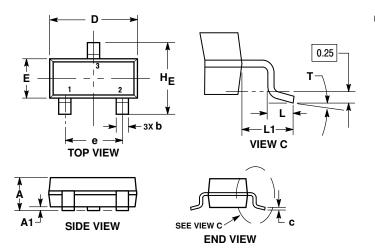


Figure 12. Capacitance

Figure 10. Current-Gain — Bandwidth Product

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- THE BASE MATERIAL.

  DIMENSIONS O AND E DO NOT INCLUDE MOLD FLASH,

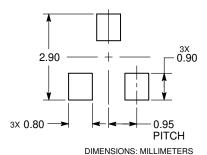
  PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

#### STYLE 6:

- PIN 1. BASE 2. EMITTER
  - COLLECTOR

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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